

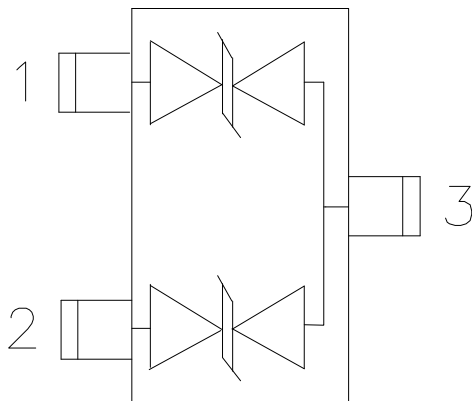
Description

The DFMSM24C is a bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The DFMSM24C complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Mechanical Characteristics

- ◆ Package: SOT-23
- ◆ Lead Finish: Matte Tin
- ◆ Case Material: "Green" Molding Compound.
- ◆ Moisture Sensitivity: Level 3 per J-STD-020
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

Dimensions and Pin Configuration



Circuit and Pin Schematic

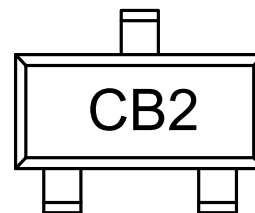
Features

- ◆ Protects two uni-directional lines
- ◆ Ultra low leakage: nA level
- ◆ Operating voltage: 24V
- ◆ Low clamping voltage
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lighting) 8A (8/20 μs)
- ◆ RoHS Compliant

Applications

- ◆ Cellular Handsets and Accessories
- ◆ Notebook and Handhelds
- ◆ Portable Instrumentation
- ◆ Set Top Box
- ◆ Industrial Controls
- ◆ Server and Desktop PC

Marking Information



CB2 = Device Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
DFMSM24C	CB2	3000/Tape & Reel	7 inch

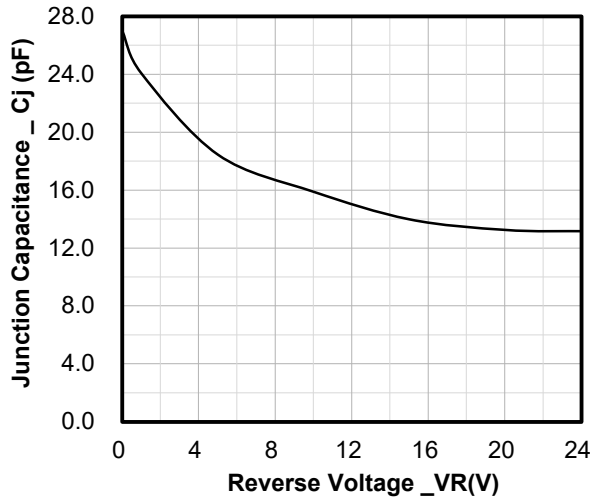
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	400	W
Peak Pulse Current (8/20 μs)	Ipp	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	± 30 ± 30	kV
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

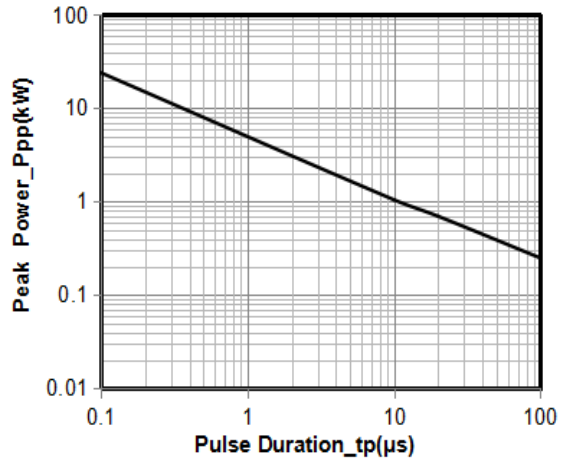
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	26.70			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I _R			200	nA	VRWM = 24V
Clamping Voltage	VC			35	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	VC			45	V	I _{PP} = 8A (8 x 20 μs pulse)
Junction Capacitance	CJ		26		pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

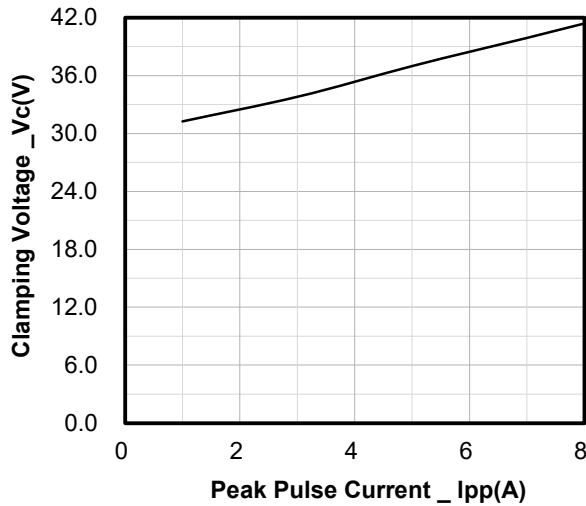
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



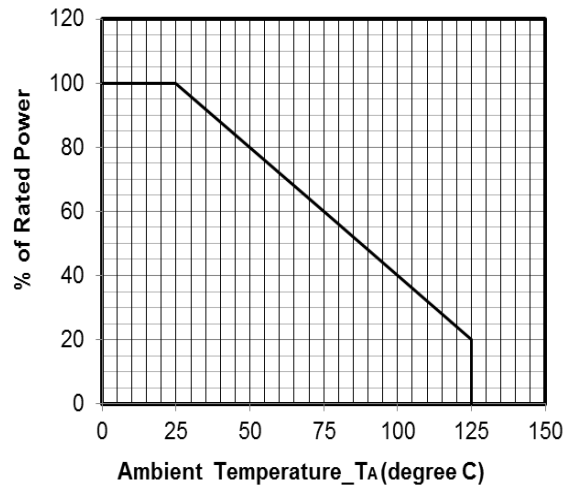
Junction Capacitance vs. Reverse Voltage



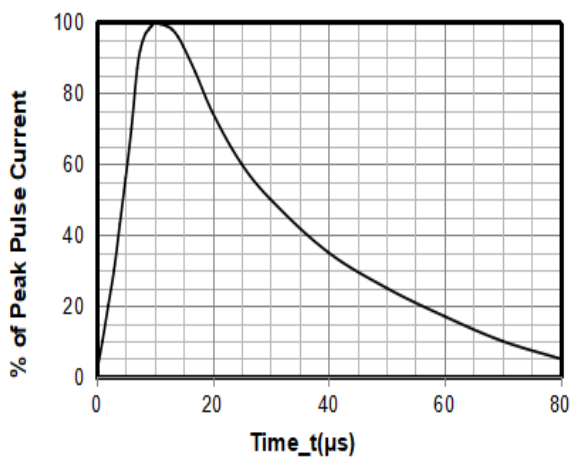
Peak Pulse Power vs. Pulse Time



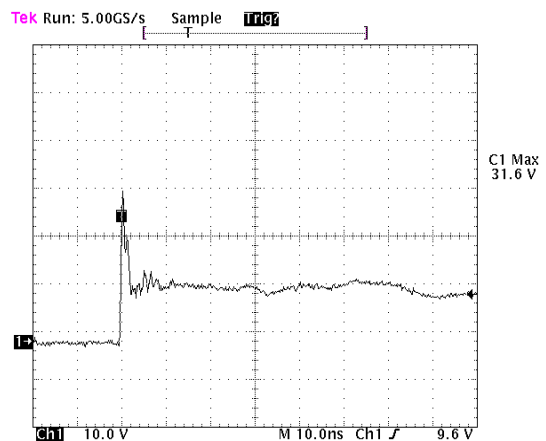
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

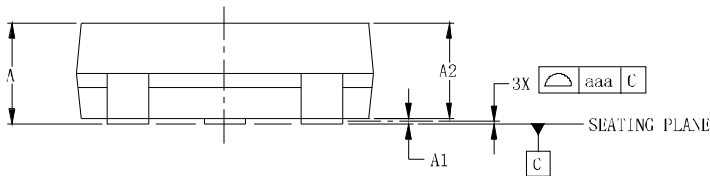
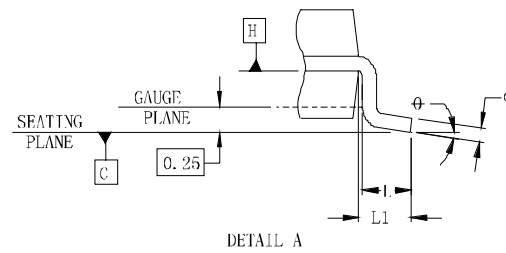
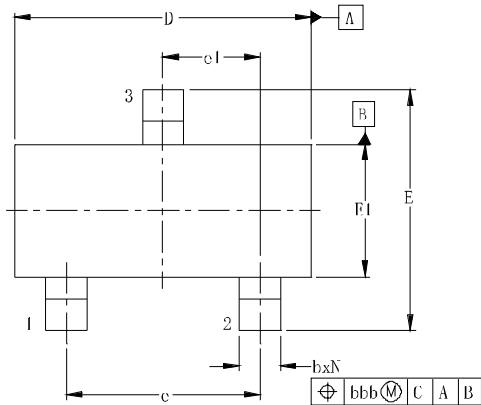


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

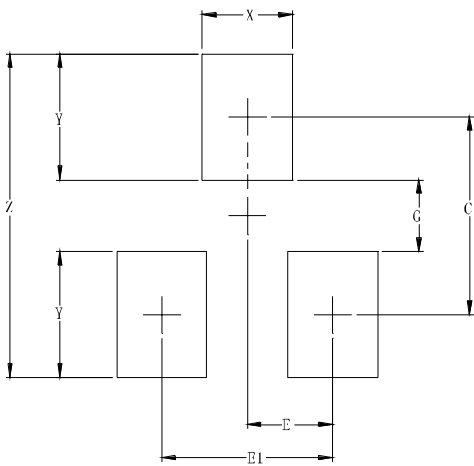
8 kV Contact per IEC61000-4-2

SOT-23 Package Outline Drawing



DIMENSIONS						
SYM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	-	0.044	0.89	-	1.12
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
c	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075			1.90BSC		
e1	0.037			0.95BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022			0.55		
N	3			3		
ϕ	0°	-	8°	0°	-	8°
aaa	0.004			0.10		
bbb	0.008			0.20		

Suggested Land Pattern



DIMENSIONS		
SYM	INCHES	MILLIMETERS
C	0.087	2.20
E	0.037	0.95
E1	0.075	1.90
G	0.031	0.80
X	0.039	1.00
Y	0.055	1.40
Z	0.141	3.60

Contact Information

Changzhou D-first Electronics CO.,Ltd.

www.first-electronic.com

Email: xhf@first-electronic.cn

Phone: +86 (0519) 8817 1671